

**AMENDMENTS TO THE SPECIFICATION**

Please replace the original "Brief Description of the Drawings" section, with the following amended "Brief Description of the Drawings" section:

**BRIEF DESCRIPTION OF THE DRAWINGS**

The present invention will be understood and appreciated more fully from the following detailed description taken in conjunction with the drawings in which:

Figure 1 is a cross section of a first step for realizing the circuit structure according to the present invention;

Figure 2 is a cross section of a second step for realizing the circuit structure according to the present invention;

Figure 3 is a cross section of a third step for realizing the circuit structure according to the present invention;

Figure 4 is a cross section of a fourth step for realizing the circuit structure according to the present invention;

Figure 5 is a cross section of a fifth step for realizing the circuit structure according to the present invention;

Figure 6 is a cross section of a sixth step for realizing the circuit structure according to the present invention; [[and]]

Figure 7 is a cross section of a seventh step for realizing the circuit structure according to the present invention; and

Figure 8 shows an embodiment where the integrated circuit structure comprises an N type substrate and P+ type buried silicon regions.

Preliminary Amendment  
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Please add the following new paragraph on page 9, beginning at line 16, after the paragraph on lines 6-15:

Figure 8 shows an embodiment where the integrated circuit structure comprises an N type substrate and P+ type buried silicon regions.